

Sujay B Desai

List of Publications by Year in descending order

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Version: 2024-02-01

17
papers

4,155
citations

687363

13
h-index

940533

16
g-index

17
all docs

17
docs citations

17
times ranked

7445
citing authors

#	ARTICLE	IF	CITATIONS
1	MoS ₂ transistors with 1-nanometer gate lengths. <i>Science</i> , 2016, 354, 99-102.	12.6	1,140
2	Strong interlayer coupling in van der Waals heterostructures built from single-layer chalcogenides. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2014, 111, 6198-6202.	7.1	970
3	Field-Effect Transistors Built from All Two-Dimensional Material Components. <i>ACS Nano</i> , 2014, 8, 6259-6264.	14.6	582
4	Strain-Induced Indirect to Direct Bandgap Transition in Multilayer WSe ₂ . <i>Nano Letters</i> , 2014, 14, 4592-4597.	9.1	572
5	Gold-Mediated Exfoliation of Ultralarge Optoelectronically-Perfect Monolayers. <i>Advanced Materials</i> , 2016, 28, 4053-4058.	21.0	307
6	Large-area and bright pulsed electroluminescence in monolayer semiconductors. <i>Nature Communications</i> , 2018, 9, 1229.	12.8	146
7	Monolithic 3D CMOS Using Layered Semiconductors. <i>Advanced Materials</i> , 2016, 28, 2547-2554.	21.0	107
8	MoS ₂ Heterojunctions by Thickness Modulation. <i>Scientific Reports</i> , 2015, 5, 10990.	3.3	93
9	Air stable <i>n</i> -doping of WSe ₂ by silicon nitride thin films with tunable fixed charge density. <i>APL Materials</i> , 2014, 2, .	5.1	76
10	Direct growth of single-crystalline III-V semiconductors on amorphous substrates. <i>Nature Communications</i> , 2016, 7, 10502.	12.8	45
11	Highly Sensitive Bulk Silicon Chemical Sensors with Sub-5 nm Thin Charge Inversion Layers. <i>ACS Nano</i> , 2018, 12, 2948-2954.	14.6	41
12	Spatially Precise Transfer of Patterned Monolayer WS ₂ and MoS ₂ with Features Larger than 10 ⁴ μm ² Directly from Multilayer Sources. <i>ACS Applied Electronic Materials</i> , 2019, 1, 407-416.	4.3	23
13	Ultrafast Spontaneous Emission from a Slot-Antenna Coupled WSe ₂ Monolayer. <i>ACS Photonics</i> , 2018, 5, 2701-2705.	6.6	17
14	Bright electroluminescence in ambient conditions from WSe ₂ p-n diodes using pulsed injection. <i>Applied Physics Letters</i> , 2019, 115, 011103.	3.3	13
15	2D layered materials: From materials properties to device applications. , 2015, , .		9
16	High-gain monolithic 3D CMOS inverter using layered semiconductors. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	8
17	Gate Quantum Capacitance Effects in Nanoscale Transistors. <i>Nano Letters</i> , 2019, 19, 7130-7137.	9.1	6